

**BYW77G-200**

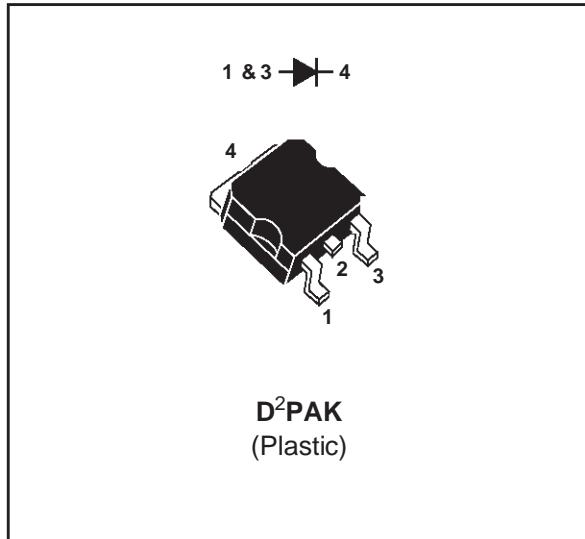
HIGH EFFICIENCY FAST RECOVERY DIODES

MAIN PRODUCT CHARACTERISTICS

I _{F(AV)}	25 A
V _{RRM}	200 V
t _{rr}	50 ns
V _F	0.85 V

FEATURES AND BENEFITS

- VERY SMALL CONDUCTION LOSSES
- NEGLIGIBLE SWITCHING LOSSES
- LOW FORWARD AND REVERSE RECOVERY TIME
- HIGH SURGE CURRENT CAPABILITY
- SMD PACKAGE



DESCRIPTION

Single rectifier suited for switchmode power supply and high frequency DC to DC converters.
Packaged in D²PAK, this surface mount device is intended for use in high frequency inverters, free wheeling and polarity protection applications.

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter		Value	Unit
V _{RRM}	Repetitive peak reverse voltage		200	V
I _{F(RMS)}	RMS forward current		50	A
I _{F(AV)}	Average forward current	T _c =125°C δ = 0.5	25	A
I _{FSM}	Surge non repetitive forward current	tp=10ms sinusoidal	200	A
I _{FRM}	Repetitive peak forward current	tp = 5μs f = 5 kHz	310	A
T _{tsg} T _j	Storage and junction temperature range		- 40 to + 150	°C

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THERMAL RESISTANCE

Symbol	Parameter	Value	Unit
R _{th} (j-c)	Junction to case	1	°C/W

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test Conditions		Min.	Typ.	Max.	Unit
I _R *	Reverse leakage current	V _R = V _{RRM}	T _j = 25°C			25	μA
			T _j = 100°C			2.5	mA
V _F **	Forward voltage drop	I _F = 20 A	T _j = 125°C			0.85	V
		I _F = 40 A	T _j = 125°C			1.00	
		I _F = 40 A	T _j = 25°C			1.15	

Pulse test : * tp = 5 ms, δ < 2 %

** tp = 380 μs, δ < 2 %

To evaluate the conduction losses use the following equation:

$$P = 0.65 \times I_F(AV) + 0.0075 I_F^2(RMS)$$

RECOVERY CHARACTERISTICS

Symbol	Parameter	Test Conditions		Min.	Typ.	Max.	Unit
t _{rr}	Reverse recovery time	T _j = 25°C I _{rr} = 0.25 A	I _F = 0.5A I _R = 1A			35	ns
		T _j = 25°C dI/dt = -50A/μs	I _F = 1A VR = 30V			50	
t _{fr}	Forward recovery time	T _j = 25°C dI/dt = 100A/μs VFR = 1.1 x VF max	I _F = 1A		10		ns
V _{FP}	Peak forward voltage	T _j = 25°C dI/dt = 100A/μs	I _F = 1A		1.5		V

PIN OUT configuration in D²PAK:

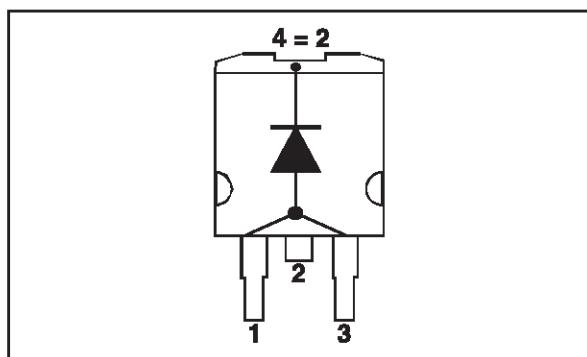


Fig.1 : Average forward power dissipation versus average forward current.

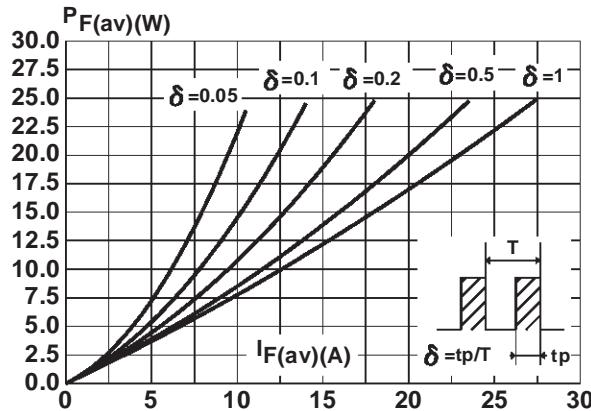


Fig.3 : Forward voltage drop versus forward current (maximum values).

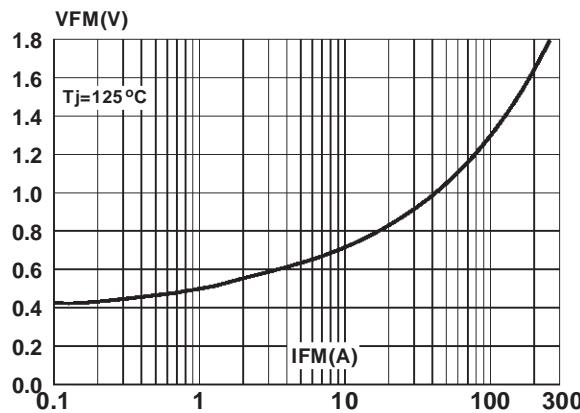


Fig.5 : Non repetitive surge peak forward current versus overload duration.

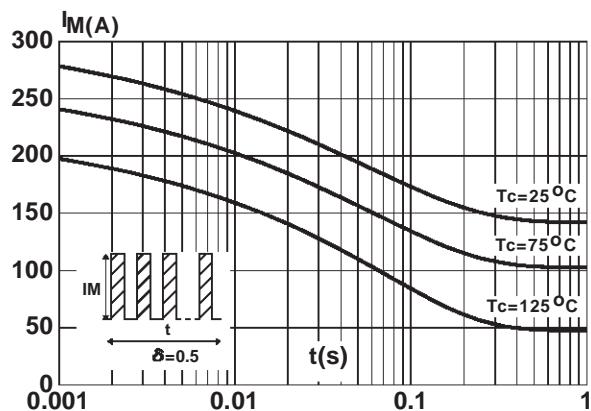


Fig.2 : Peak current versus form factor.

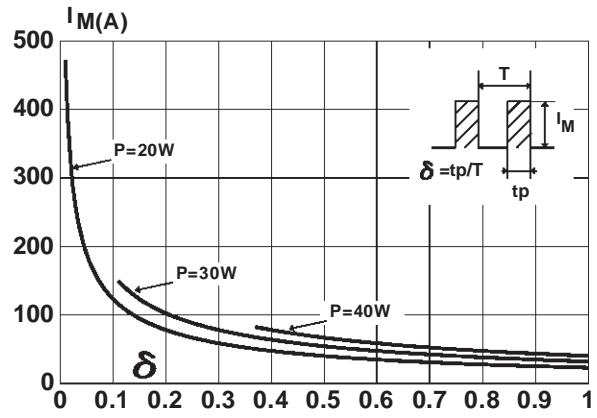


Fig.4 : Relative variation of thermal impedance junction to case versus pulse duration.

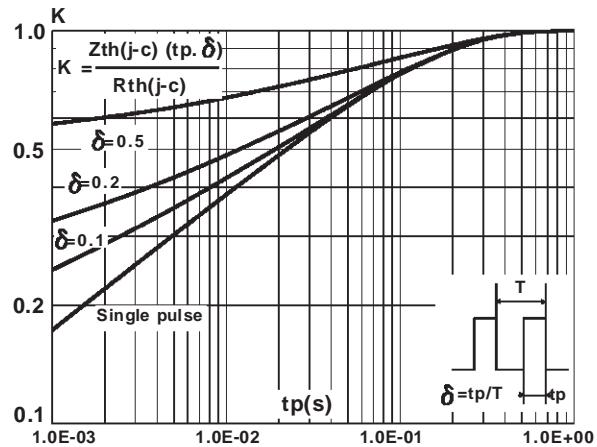
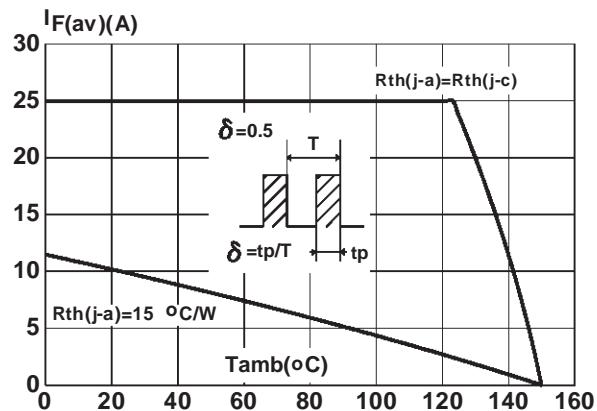


Fig.6 : Average current versus ambient temperature. ($\delta = 0.5$)



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Fig.7 : Junction capacitance versus reverse voltage applied (Typical values).

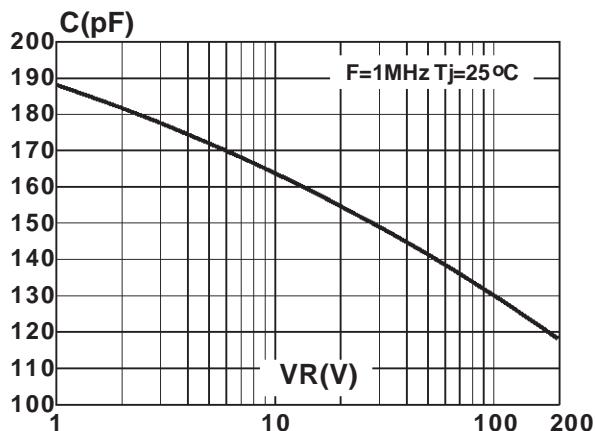


Fig.9 : Peak reverse current versus dI_F/dt .

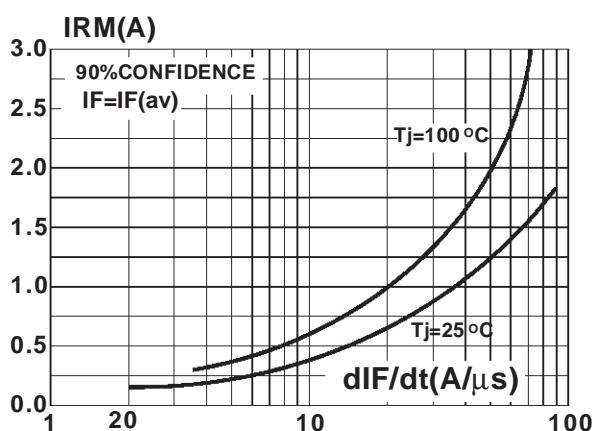


Fig.8 : Reverse recovery charges versus dI_F/dt .

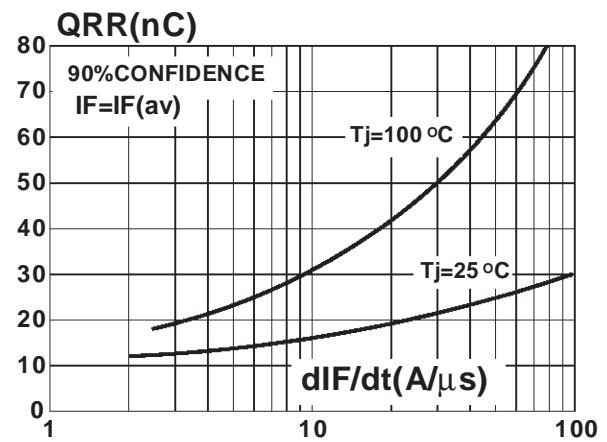
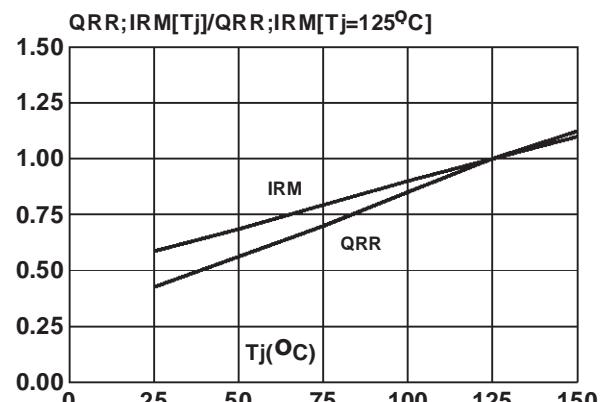
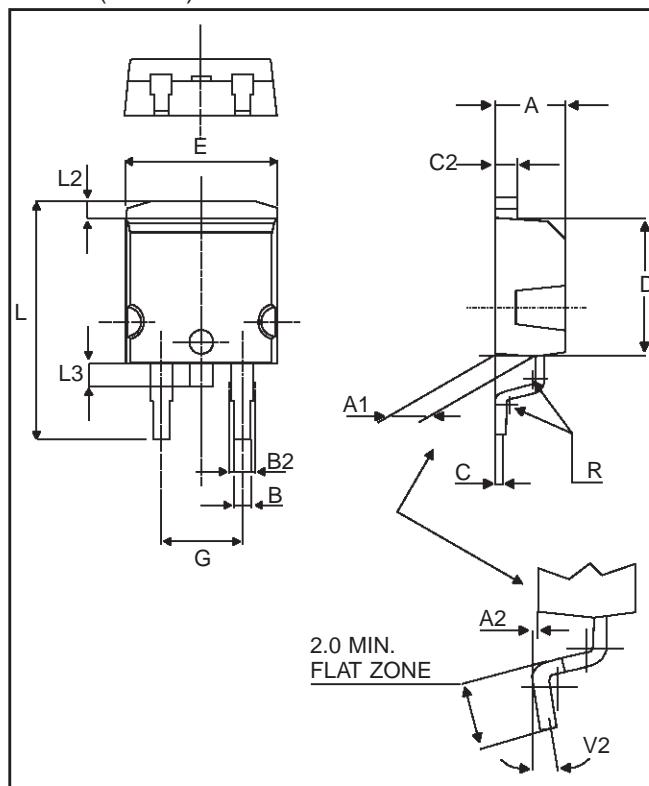


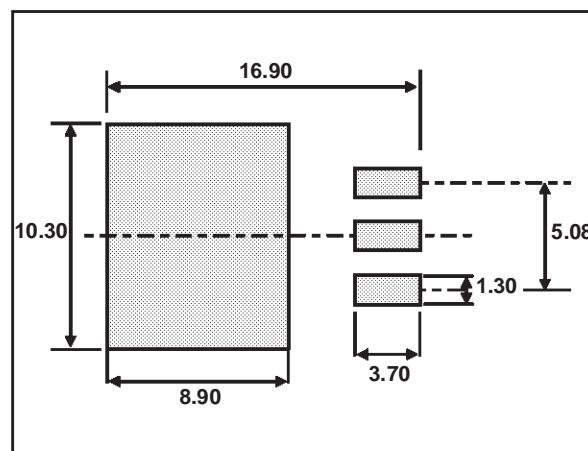
Fig.10 : Dynamic parameters versus junction temperature.



PACKAGE MECHANICAL DATA
D²PAK (Plastic)



REF.	DIMENSIONS					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.30		4.60	0.169		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
B	0.70		0.93	0.027		0.037
B2	1.25	1.40		0.049	0.055	
C	0.45		0.60	0.017		0.024
C2	1.21		1.36	0.047		0.054
D	8.95		9.35	0.352		0.368
E	10.00		10.28	0.393		0.405
G	4.88		5.28	0.192		0.208
L	15.00		15.85	0.590		0.624
L2	1.27		1.40	0.050		0.055
L3	1.40		1.75	0.055		0.069
R		0.40			0.016	
V2	0°		8°	0°		8°

FOOT PRINT (in millimeters)


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